

	No.4231	2SJ254
		P-Channel MOS Silicon FET Very High-Speed Switching Applications

Features

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.
- Micaless package facilitating mounting.

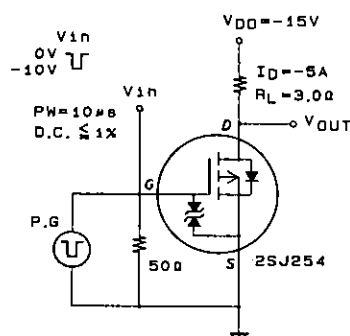
Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

			unit
Drain to Source Voltage	V_{DS}	-30	V
Gate to Source Voltage	V_{GS}	± 15	V
Drain Current(DC)	I_D	-8	A
Drain Current(Pulse)	I_{DP}	$PW \leq 10\mu s, \text{ duty cycle} \leq 1\%$	-32 A
Allowable Power Dissipation	P_D	2.0	W
		$T_c = 25^\circ\text{C}$	25 W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

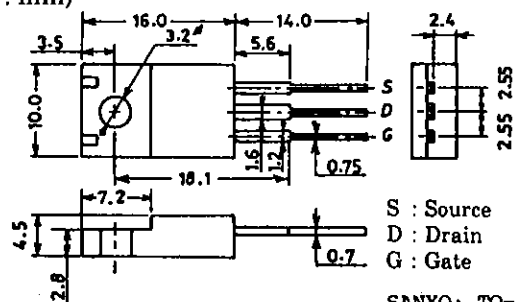
Electrical Characteristics at $T_a = 25^\circ\text{C}$

			min	typ	max	unit
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1\text{mA}, V_{GS} = 0$	-30			V
G-S Breakdown Voltage	$V_{(BR)GSS}$	$I_G = \pm 100\mu A, V_{DS} = 0$	± 15			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30\text{V}, V_{GS} = 0$			-100	μA
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 12\text{V}, V_{DS} = 0$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10\text{V}, I_D = -1\text{mA}$	-1.0		-2.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = -10\text{V}, I_D = -5\text{A}$	4	6.5		S
Static Drain to Source on State Resistance	$R_{DS(on)}$	$I_D = -5\text{A}, V_{GS} = -10\text{V}$		85	120	$m\Omega$
	$R_{DS(on)}$	$I_D = -5\text{A}, V_{GS} = -4\text{V}$		120	170	$m\Omega$
Input Capacitance	C_{iss}	$V_{DS} = -10\text{V}, f = 1\text{MHz}$		1000		pF
Output Capacitance	C_{oss}	$V_{DS} = -10\text{V}, f = 1\text{MHz}$		600		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = -10\text{V}, f = 1\text{MHz}$		220		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		15		ns
Rise Time	t_r	"		80		ns
Turn-OFF Delay Time	$t_{d(off)}$	"		120		ns
Fall Time	t_f	"		170		ns
Diode Forward Voltage	V_{SD}	$I_S = -8\text{A}, V_{GS} = 0$	-1.0	-1.5		V

Switching Time Test Circuit



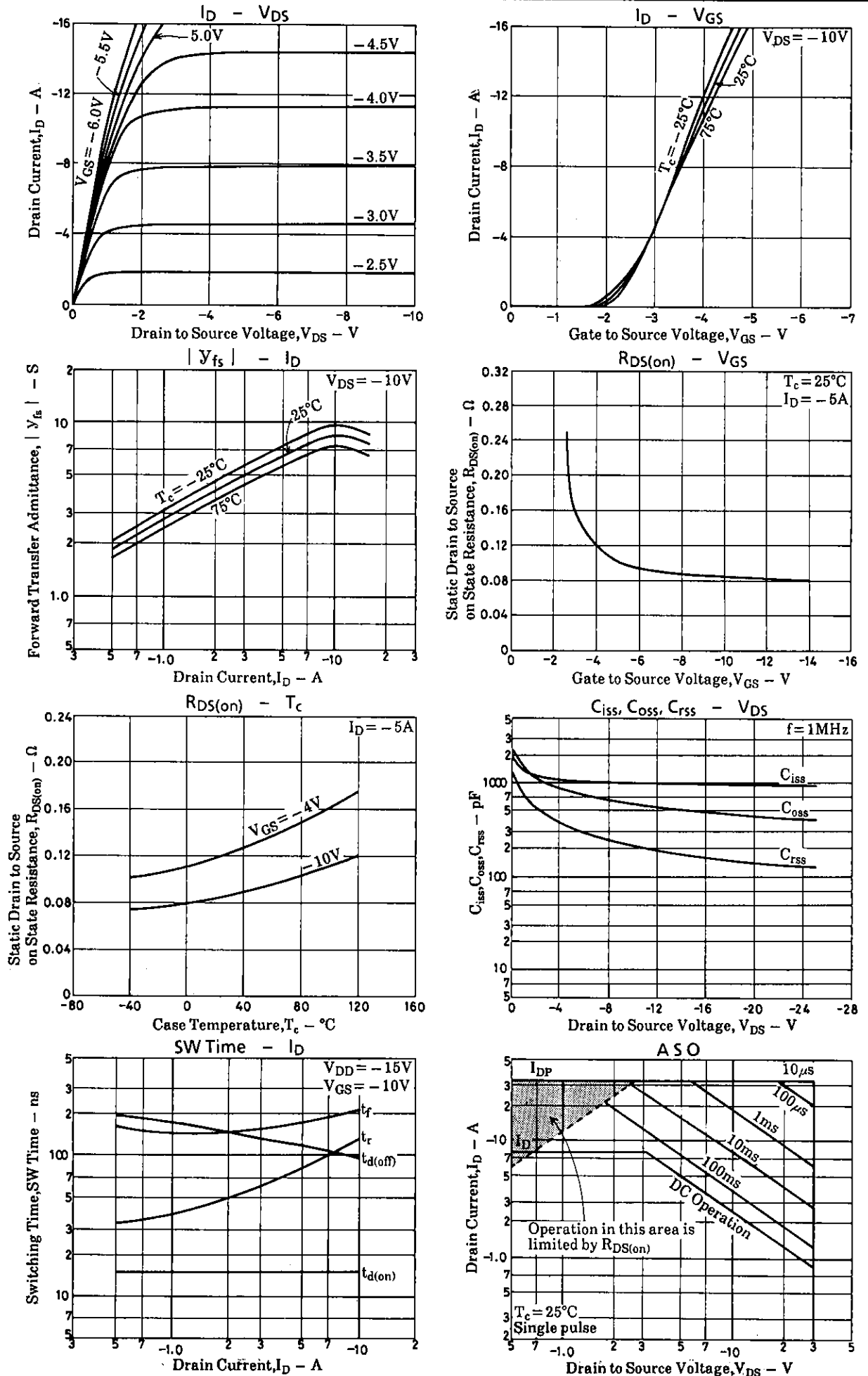
Package Dimensions 2063 (unit : mm)

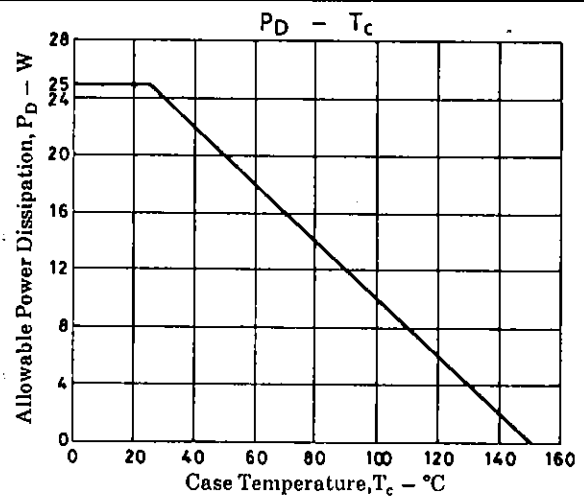
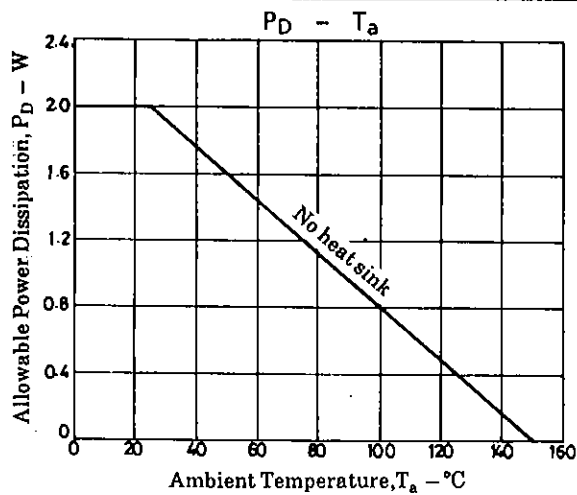


S : Source
D : Drain
G : Gate

SANYO: TO-220ML

SANYO Electric Co., Ltd. Semiconductor Business Headquarters
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN





- No products described or contained herein are intended for use in surgical implants, life-support systems, aerospace equipment, nuclear power control systems, vehicles, disaster/crime-prevention equipment and the like, the failure of which may directly or indirectly cause injury, death or property loss.
- Anyone purchasing any products described or contained herein for an above-mentioned use shall:
 - ① Accept full responsibility and indemnify and defend SANYO ELECTRIC CO., LTD., its affiliates, subsidiaries and distributors and all their officers and employees, jointly and severally, against any and all claims and litigation and all damages, cost and expenses associated with such use:
 - ② Not impose any responsibility for any fault or negligence which may be cited in any such claim or litigation on SANYO ELECTRIC CO., LTD., its affiliates, subsidiaries and distributors or any of their officers and employees jointly or severally.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. SANYO believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.